

3.048mm Silicon PD Chip datasheet

P/N : WS9E-01C

Application

Si PIN photodiode chip

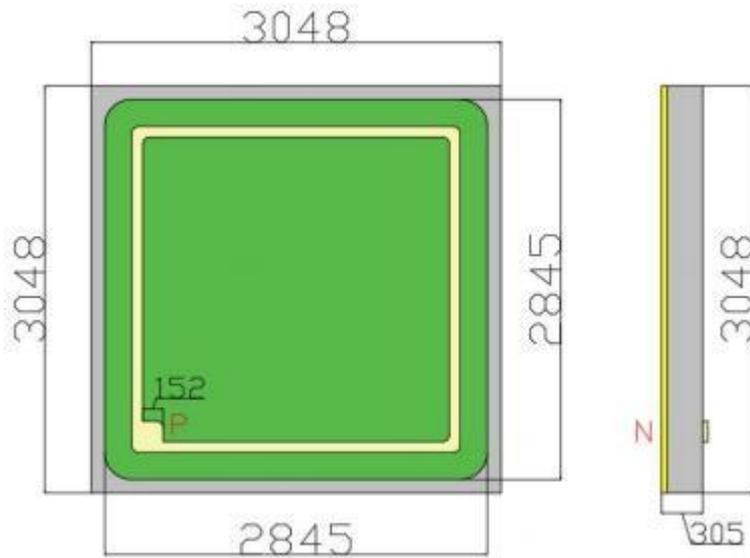
Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	2845±20 x 2845±20			µm
Chip width	3048			µm
Chip length	3048			µm
Chip height	285	305	325	µm
Pad Area		152		µm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100µA, H=0	35			V
Reverse Dark Current	Id	Vr=10V			10	nA
Sensitive Wavelength Range	λ		400	940	1100	nm
Capacitance	Cj	VR=5V, f=1MHz		16		pF